

**AMENDMENTS TO THE SPECIFICATION:**

**Please amend this application on page 1, line 1, by inserting the following new paragraph:**

This is a divisional of Application No. 10/303,855, filed November 26, 2002, which is incorporated herein by reference in its entirety.

**Please replace the paragraph on page 3, beginning line 9 with the following paragraph:**

Further, since the surface of a Cu layer being polished is also hydrophobic, residual abrasion dust is caused to adhere onto the surface of the Cu layer. Further, since the Cu layer is polished in the presence of residual abrasion dust, scratches are caused to generate on the surface of the Cu layer.

**Please replace the paragraph on page 3, beginning line 15 with the following paragraph:**

Therefore, it is required that the protective film made of an organic Cu complex is made hydrophilic. It is conceivable to incorporate a surfactant into the complexing agent in order to hydrophilize the protective film formed of an organic Cu complex. However, if the surfactant is formed of an ionic surfactant, the surfactant may react with Cu to form a compound or be adsorbed onto the particles in the polishing slurry, thereby deteriorating the performance of CMP. On the other hand, if the surfactant is formed of a nonionic surfactant, the surfactant may be prevented from forming a complex with Cu, thus allowing the surfactant to adsorb onto a hydrophobic organic complex that may be

formed through the reaction between Cu and the complexing agent, thereby improving, to some extent, the hydrophilicity of the protective film. However, since the magnitude of hydrophilization of the protective film is insufficient in this case, the effect obtained from this hydrophilization of the protective film would be negligible.

**Please replace the paragraph on page 5, beginning line 21 with the following paragraph:**

FIG. 3 is a graph illustrating the results measured of the polishing rate of the Cu layer and of the magnitude of erosion of the Cu layer, both of which are obtained while changing the mixing ratio ~~to~~ of quinaldinic acid to quinolinic acid;

**Please replace the paragraph on page 11, line 14 to page 12 line 6 with the following paragraph:**

FIG. 5 illustrates the chemical formula representing the chemical structure of the Cu complex which has been formed using quinaldinic acid as the first complexing agent, and quinolinic acid as the second complexing agent. Namely, as shown in FIG. 5, two kinds of complexes, i.e., a complex where both of quinaldinic acid and ~~quinolinic~~ quinolinic acid are coordinately bonded to Cu, and a complex where only quinaldinic acid is coordinately bonded to Cu are mixedly included in the protective film.

**Please replace the paragraph on page 21, beginning line 10 with the following paragraph:**

As a result, it was possible to perform the polishing in such manners that the polishing speed of Cu was 1000nm/min, that the magnitude of erosion (the width of wiring: 50  $\mu$ m) was suppressed to <30nm, that the polishing stability was improved, and

that high-quality polishing where the surface of the wafer was free from the generation of any defects was achieved.

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